

Description

The SX80N03DF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = 30V$ $I_D = 80A$

$R_{DS(ON)} < 4.0m\Omega$ $V_{GS}=10V$

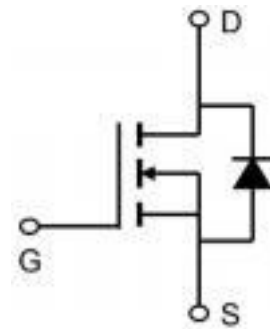
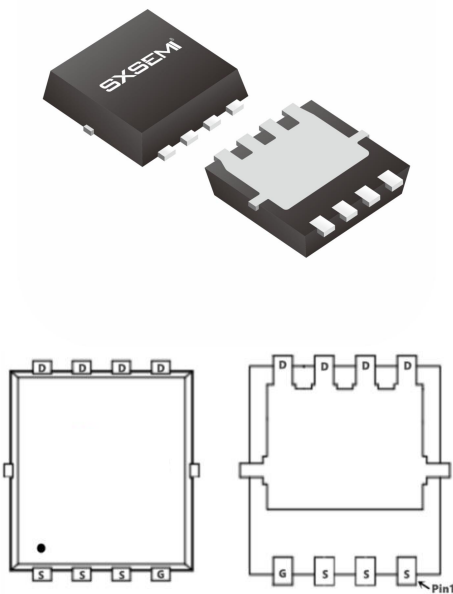
Application

Battery protection

Load switch

Uninterruptible power supply

PDFN3*3-8L



Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	65	A
I_{DM}	Pulsed Drain Current ²	360	A
EAS	Single Pulse Avalanche Energy ³	144.7	mJ
I_{AS}	Avalanche Current	53.8	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	43.4	W
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	1.67	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	2.3	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V,$	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	$V_{GS}=10V, I_D=30A$	-	3.3	4.0	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	4.3	6.0	
Ciss	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1.0MHz$	-	2680	-	pF
Coss	Output Capacitance		-	393	-	pF
Crss	Reverse Transfer Capacitance		-	330	-	pF
Qg	Total Gate Charge	$V_{DS}=15V, I_D=30A, V_{GS}=10V$	-	30	-	nC
Qgs	Gate-Source Charge		-	7.2	-	nC
Qgd	Gate-Drain("Miller") Charge		-	10.4	-	nC
td(on)	Turn-on Delay Time	$V_{DS}=15V, I_D=30A, R_{GEN}=3\Omega, V_{GS}=10V$	-	23	-	ns
tr	Turn-on Rise Time		-	28	-	ns
td(off)	Turn-off Delay Time		-	74	-	ns
tr	Turn-off Fall Time		-	36	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	120	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	400	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=30A$	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	$I_F=20A, dI/dt=100A/\mu s$	-	28	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC

Note :

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3、The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=53.8A$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

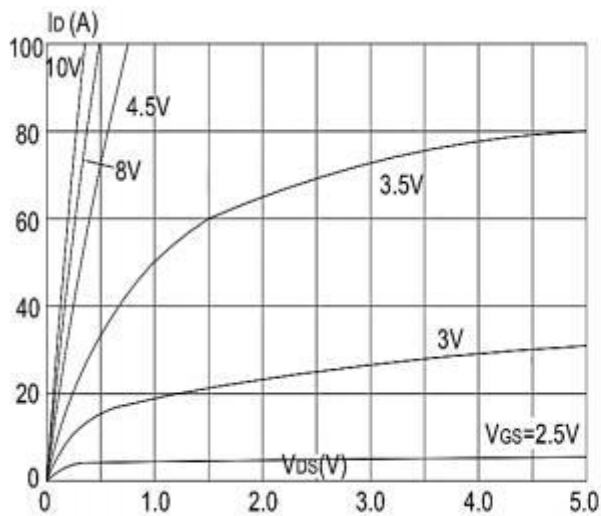


Figure1: Output Characteristics

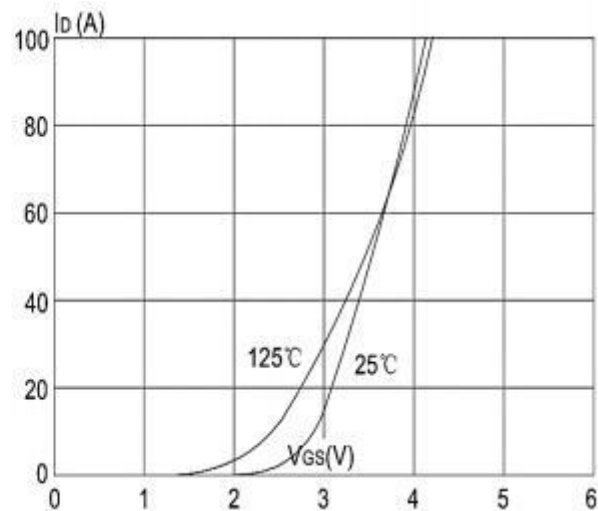


Figure 2: Typical Transfer Characteristics

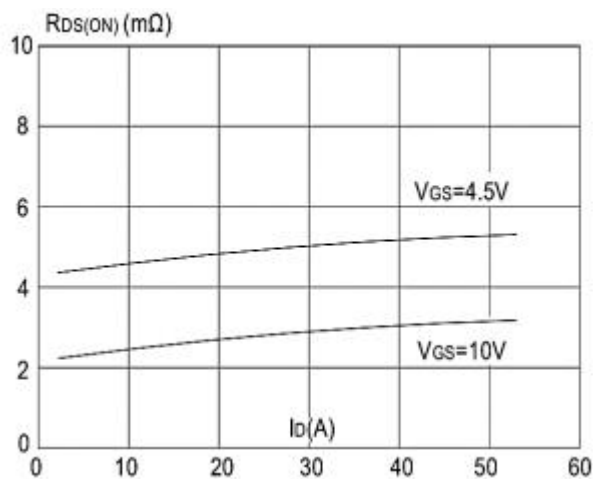


Figure 3: On-resistance vs. Drain Current

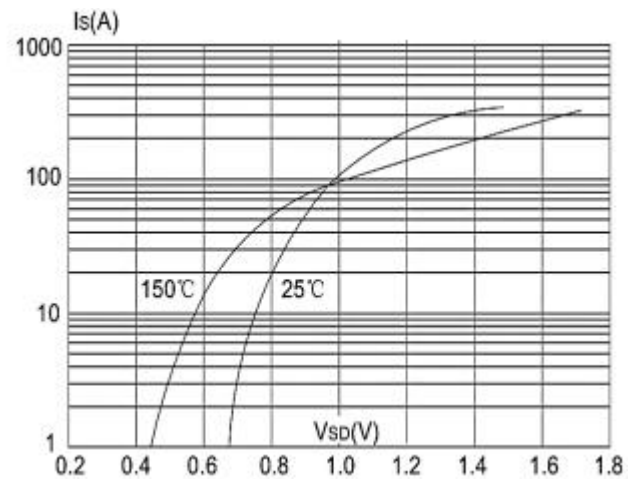


Figure 4: Body Diode Characteristics

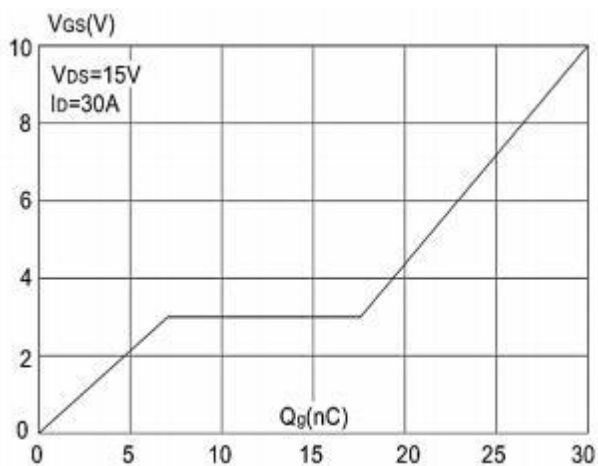


Figure 5: Gate Charge Characteristics

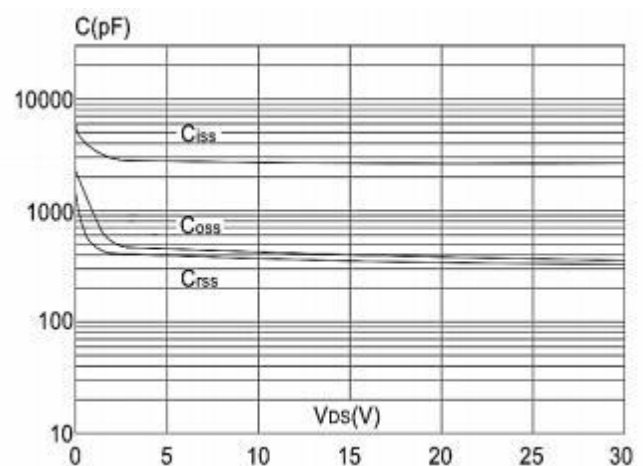


Figure 6: Capacitance Characteristics

Typical Characteristics

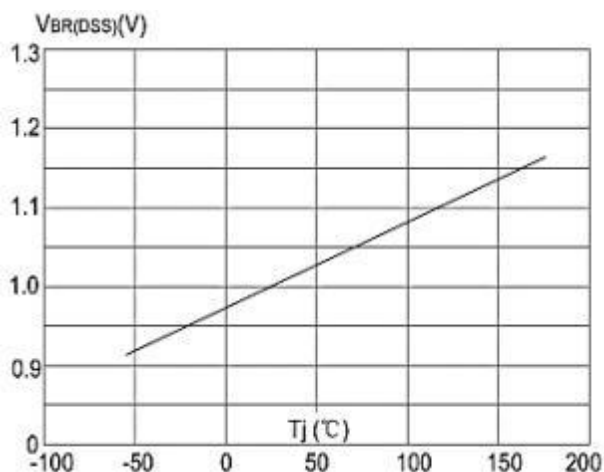


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

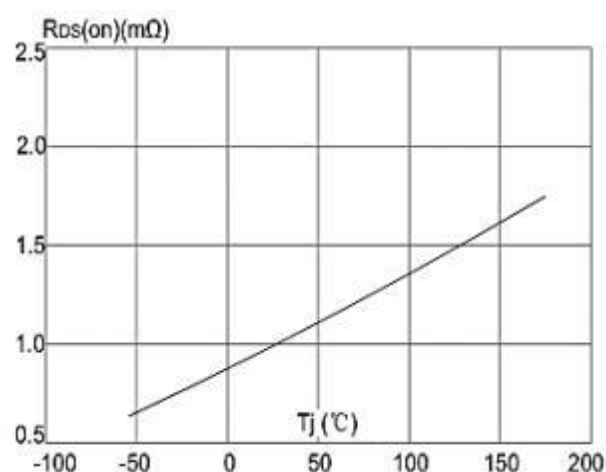


Figure 8: Normalized on Resistance vs. Junction Temperature

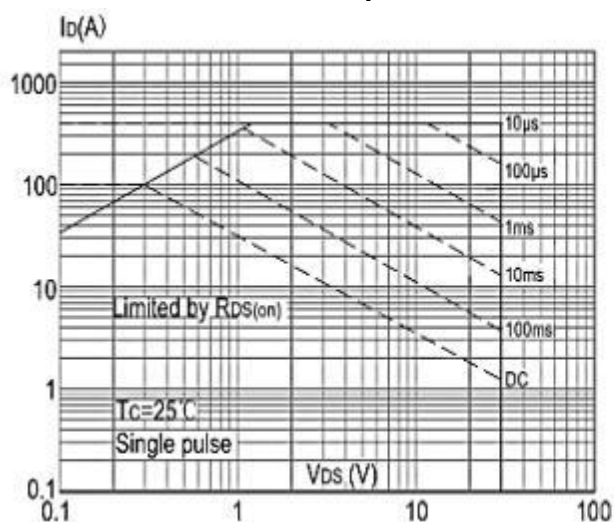


Figure 9: Maximum Safe Operating Area vs. Case Temperature

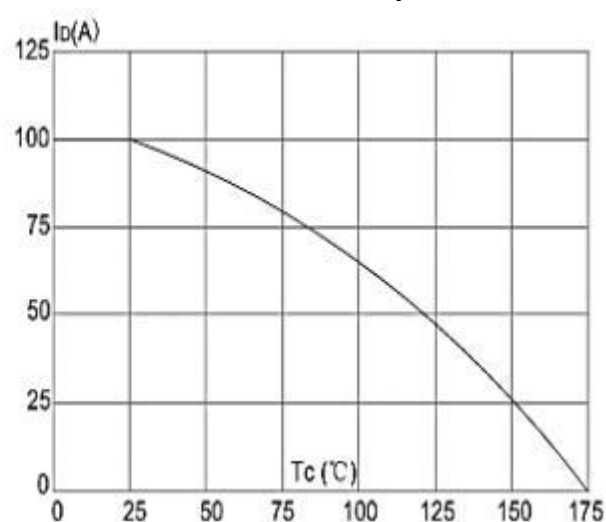


Figure 10: Maximum Continuous Drain Current

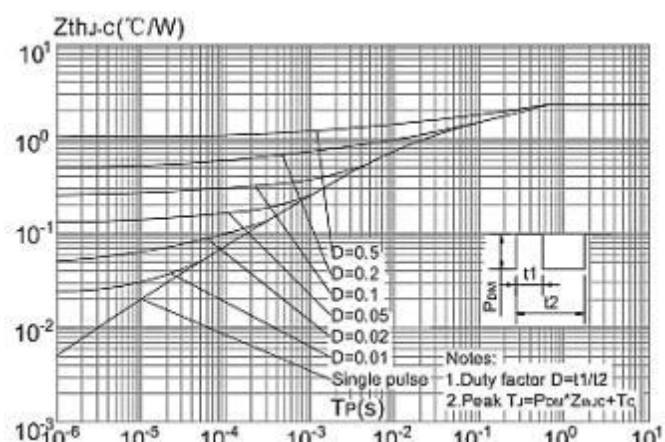
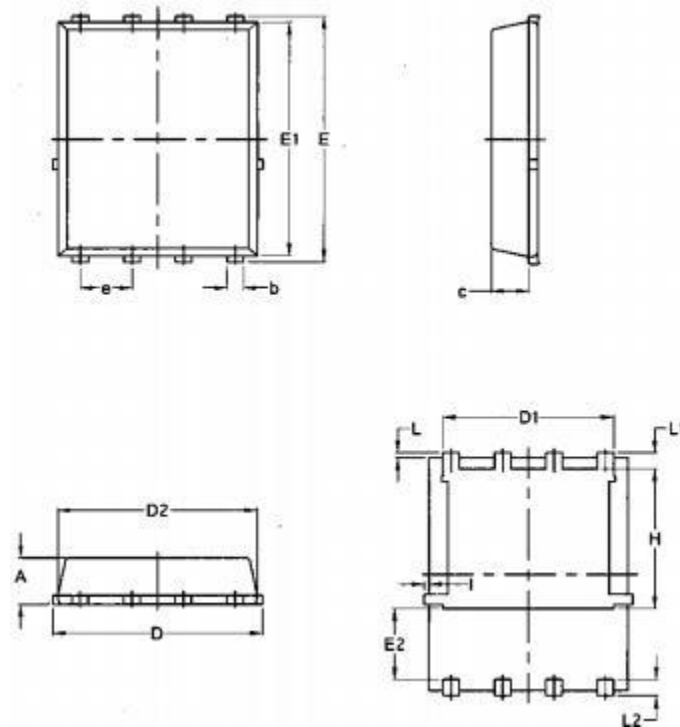


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

Package Mechanical Data-PDFN5*6-8L-JQ Single


Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	PDFN3*3-8L		5000